



**THE DATASHEET OF
MC14012BDR2**



MC14012B

Dual 4-Input NAND Gates

The MC14012B dual 4-input NAND gates are constructed with P-Channel and N-Channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

| Symbol | Parameter | Value | Unit |
|-------------------|---|------------------------|------|
| V_{DD} | DC Supply Voltage Range | -0.5 to +18.0 | V |
| V_{in}, V_{out} | Input or Output Voltage Range (DC or Transient) | -0.5 to $V_{DD} + 0.5$ | V |
| I_{in}, I_{out} | Input or Output Current (DC or Transient) per Pin | ± 10 | mA |
| P_D | Power Dissipation, per Package (Note 1) | 500 | mW |
| T_A | Ambient Temperature Range | -55 to +125 | °C |
| T_{stg} | Storage Temperature Range | -65 to +150 | °C |
| T_L | Lead Temperature (8-Second Soldering) | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Package: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



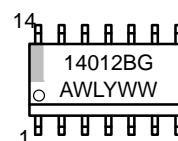
ON Semiconductor®

<http://onsemi.com>



SOIC-14
D SUFFIX
CASE 751A

MARKING DIAGRAM



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MC14012B

MC14012B Dual 4-Input NAND Gate

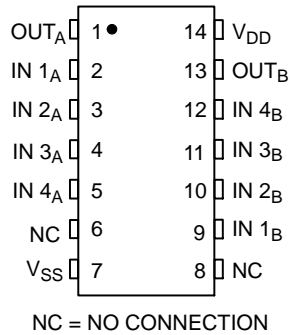


Figure 1. Pin Assignment

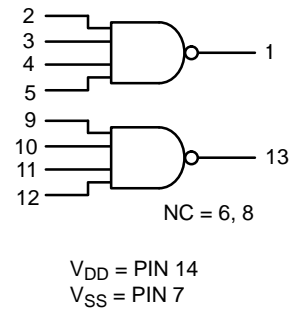


Figure 2. Logic Diagram

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------|----------------------|--------------------------|
| MC14012BDG | SOIC-14 (Pb-Free) | 55 Units / Rail |
| NLV14012BDG* | SOIC-14 (Pb-Free) | 55 Units / Rail |
| MC14012BDR2G | SOIC-14 (Pb-Free) | 2500 Units / Tape & Reel |
| NLV14012BDR2G* | SOIC-14 (Pb-Free) | 2500 Units / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

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ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

| Characteristic | Symbol | V _{DD} Vdc | -55°C | | 25°C | | | 125°C | | Unit | |
|---|---|------------------------|--|-------|-------|-----------------|------|-------|-------|------|-----|
| | | | Min | Max | Min | Typ (Note 2) | Max | Min | Max | | |
| Output Voltage V _{in} = V _{DD} or 0 | "0" Level V _{OL} | 5.0 | – | 0.05 | – | 0 | 0.05 | – | 0.05 | Vdc | |
| | | 10 | – | 0.05 | – | 0 | 0.05 | – | 0.05 | | |
| | | 15 | – | 0.05 | – | 0 | 0.05 | – | 0.05 | | |
| | "1" Level V _{in} = 0 or V _{DD} | V _{OH} | 5.0 | 4.95 | – | 4.95 | 5.0 | – | 4.95 | – | Vdc |
| | | | 10 | 9.95 | – | 9.95 | 10 | – | 9.95 | – | |
| | | | 15 | 14.95 | – | 14.95 | 15 | – | 14.95 | – | |
| Input Voltage (V _O = 4.5 or 0.5 Vdc) (V _O = 9.0 or 1.0 Vdc) (V _O = 13.5 or 1.5 Vdc) | "0" Level V _{IL} | 5.0 | – | 1.5 | – | 2.25 | 1.5 | – | 1.5 | Vdc | |
| | | 10 | – | 3.0 | – | 4.50 | 3.0 | – | 3.0 | | |
| | | 15 | – | 4.0 | – | 6.75 | 4.0 | – | 4.0 | | |
| | "1" Level (V _O = 0.5 or 4.5 Vdc) (V _O = 1.0 or 9.0 Vdc) (V _O = 1.5 or 13.5 Vdc) | V _{IH} | 5.0 | 3.5 | – | 3.5 | 2.75 | – | 3.5 | – | Vdc |
| | | | 10 | 7.0 | – | 7.0 | 5.50 | – | 7.0 | – | |
| | | | 15 | 11 | – | 11 | 8.25 | – | 11 | – | |
| Output Drive Current (V _{OH} = 2.5 Vdc) (V _{OH} = 4.6 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc) | Source I _{OH} | 5.0 | –3.0 | – | –2.4 | –4.2 | – | –1.7 | – | mAdc | |
| | | 5.0 | –0.64 | – | –0.51 | –0.88 | – | –0.36 | – | | |
| | | 10 | –1.6 | – | –1.3 | –2.25 | – | –0.9 | – | | |
| | | 15 | –4.2 | – | –3.4 | –8.8 | – | –2.4 | – | | |
| | Sink I _{OL} | 5.0 | 0.64 | – | 0.51 | 0.88 | – | 0.36 | – | mAdc | |
| | | 10 | 1.6 | – | 1.3 | 2.25 | – | 0.9 | – | | |
| 15 | | 4.2 | – | 3.4 | 8.8 | – | 2.4 | – | | | |
| Input Current | I _{in} | 15 | – | ±0.1 | – | ±0.00001 | ±0.1 | – | ±1.0 | μAdc | |
| Input Capacitance (V _{in} = 0) | C _{in} | – | – | – | – | 5.0 | 7.5 | – | – | pF | |
| Quiescent Current (Per Package) | I _{DD} | 5.0 | – | 0.25 | – | 0.0005 | 0.25 | – | 7.5 | μAdc | |
| | | 10 | – | 0.5 | – | 0.0010 | 0.5 | – | 15 | | |
| | | 15 | – | 1.0 | – | 0.0015 | 1.0 | – | 30 | | |
| Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Gate, C _L = 50 pF) | I _T | 5.0 | I _T = (0.3 μA/kHz) f + I _{DD} /N | | | | | | | μAdc | |
| 10 | I _T = (0.6 μA/kHz) f + I _{DD} /N | | | | | | | | | | |
| 15 | I _T = (0.9 μA/kHz) f + I _{DD} /N | | | | | | | | | | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

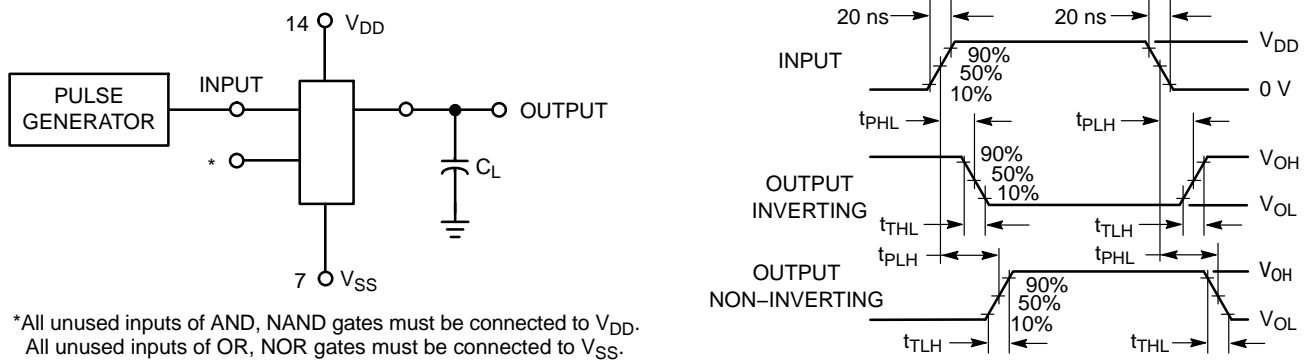
MC14012B

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}$, $T_A = 25^\circ\text{C}$)

| Characteristic | Symbol | V_{DD} Vdc | Min | Typ (Note 6) | Max | Unit |
|--|--------------------|-----------------|-------------|-----------------|-------------------|------|
| Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$ $t_{TLH} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{TLH} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$ | t_{TLH} | 5.0 10 15 | - - - | 100 50 40 | 200 100 80 | ns |
| Output Fall Time $t_{THL} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$ $t_{THL} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{THL} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$ | t_{THL} | 5.0 10 15 | - - - | 100 50 40 | 200 100 80 | ns |
| Propagation Delay Time $t_{PLH}, t_{PHL} = (0.90 \text{ ns/pF}) C_L + 115 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.36 \text{ ns/pF}) C_L + 47 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.26 \text{ ns/pF}) C_L + 37 \text{ ns}$ | t_{PLH}, t_{PHL} | 5.0 10 15 | - - - | 160 65 50 | 300 130 100 | ns |

5. The formulas given are for the typical characteristics only at 25°C .

6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.



*All unused inputs of AND, NAND gates must be connected to V_{DD} .
All unused inputs of OR, NOR gates must be connected to V_{SS} .

Figure 3. Switching Time Test Circuit and Waveforms

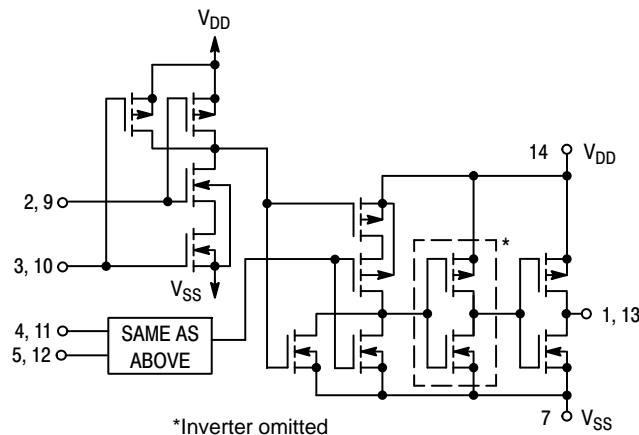


Figure 4. Circuit Schematic - One of Two Gates Shown

TYPICAL B-SERIES GATE CHARACTERISTICS

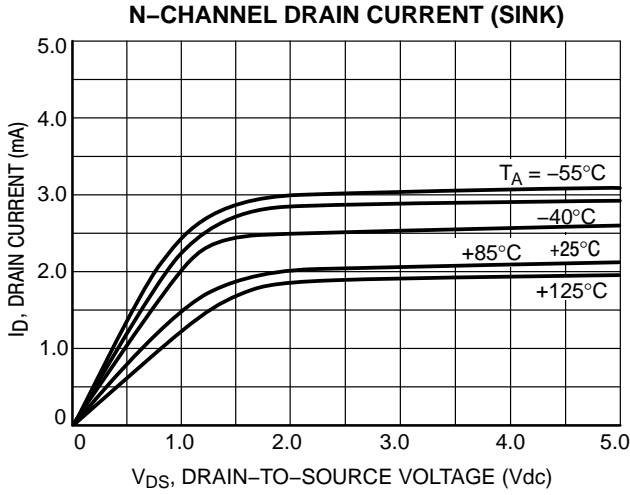


Figure 5. $V_{GS} = 5.0$ Vdc

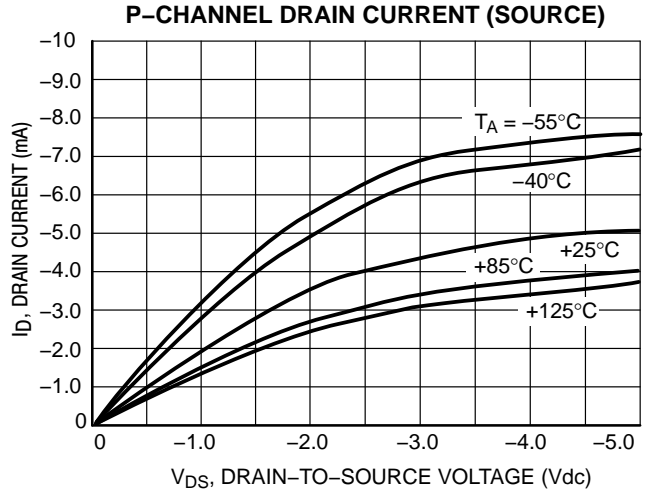


Figure 6. $V_{GS} = -5.0$ Vdc

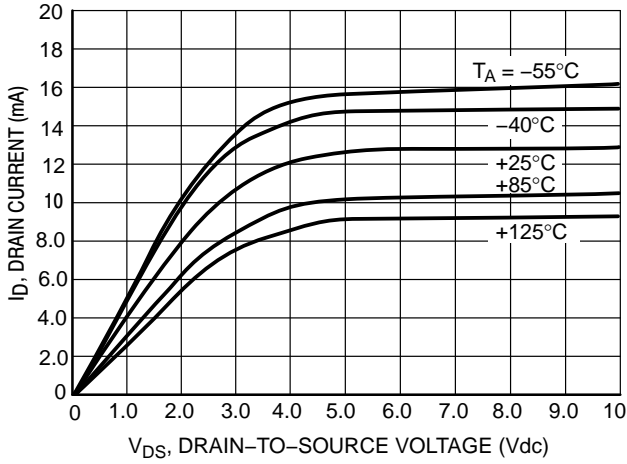


Figure 7. $V_{GS} = 10$ Vdc

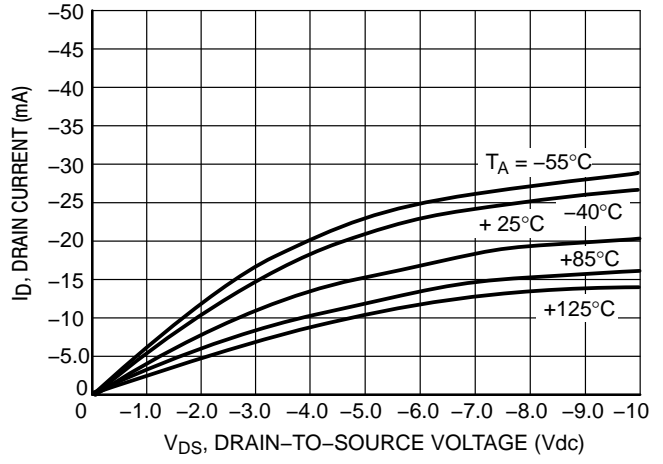


Figure 8. $V_{GS} = -10$ Vdc

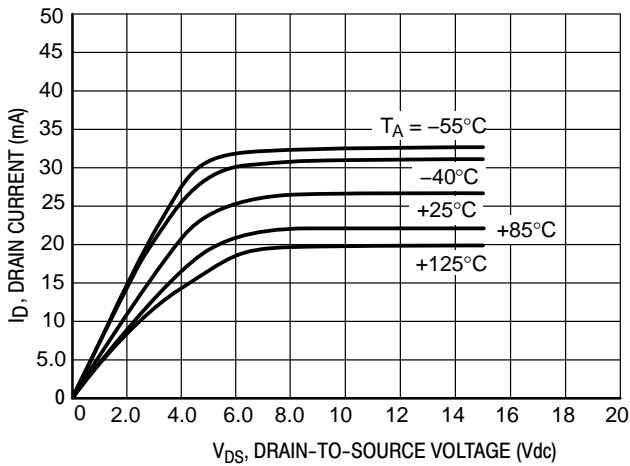


Figure 9. $V_{GS} = 15$ Vdc

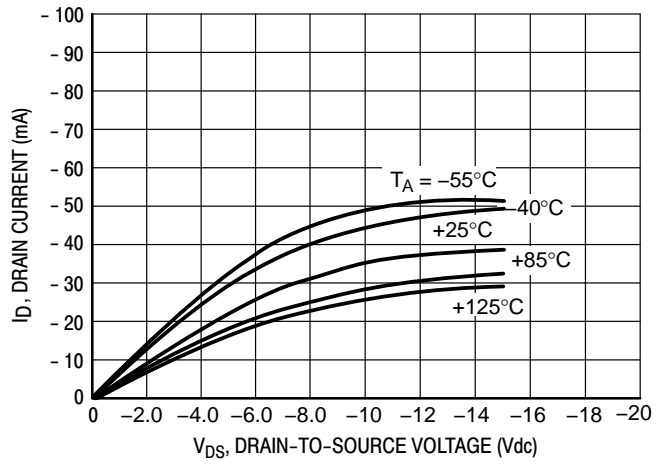


Figure 10. $V_{GS} = -15$ Vdc

These typical curves are not guarantees, but are design aids.
 Caution: The maximum rating for output current is 10 mA per pin.

VOLTAGE TRANSFER CHARACTERISTICS

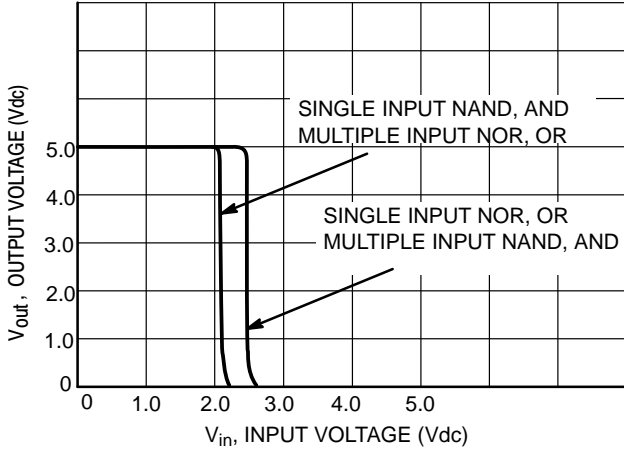


Figure 11. $V_{DD} = 5.0 \text{ Vdc}$

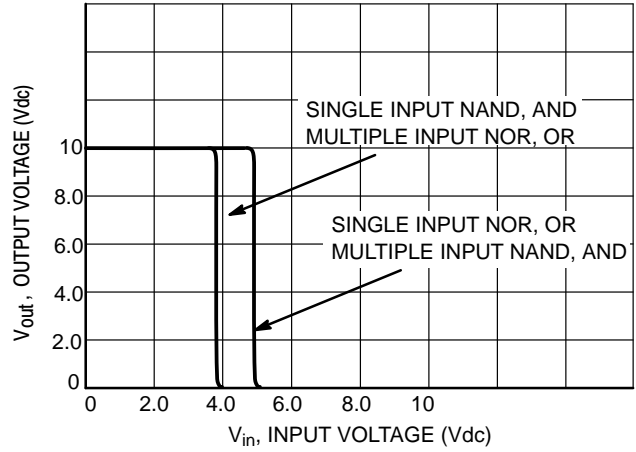


Figure 12. $V_{DD} = 10 \text{ Vdc}$

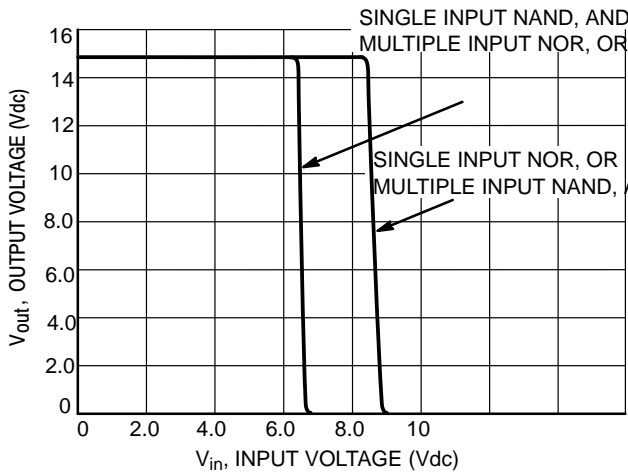


Figure 13. $V_{DD} = 15 \text{ Vdc}$

DC NOISE MARGIN

The DC noise margin is defined as the input voltage range from an ideal “1” or “0” input level which does not produce output state change(s). The typical and guaranteed limit values of the input values V_{IL} and V_{IH} for the output(s) to be at a fixed voltage V_O are given in the Electrical Characteristics table. V_{IL} and V_{IH} are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the “1” and “0” levels =

- 1.0 V with a 5.0 V supply
- 2.0 V with a 10.0 V supply
- 2.5 V with a 15.0 V supply

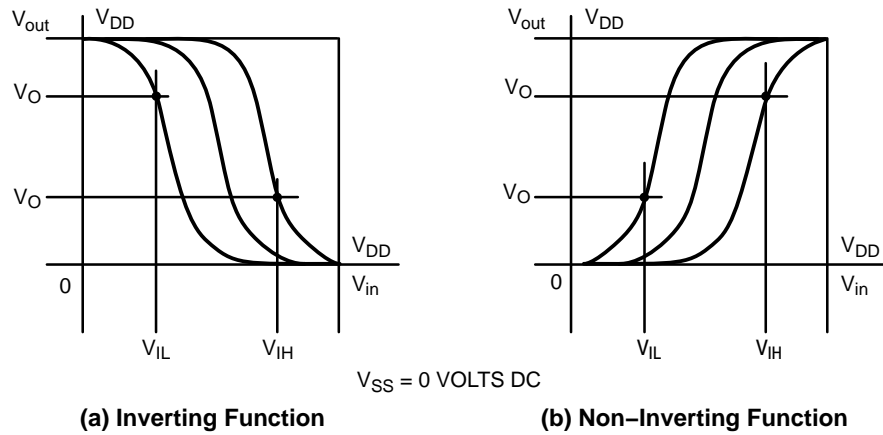
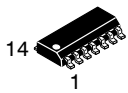


Figure 14. DC Noise Immunity

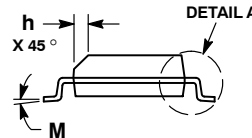
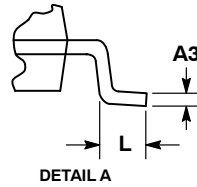
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-14 NB
CASE 751A-03
ISSUE L

DATE 03 FEB 2016

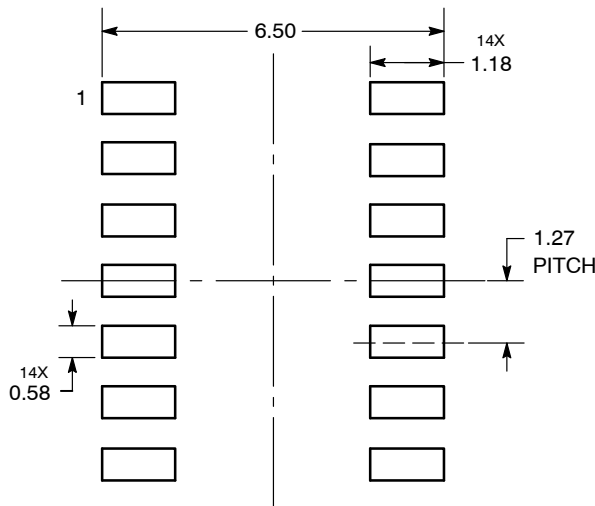


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 1.35 | 1.75 | 0.054 | 0.068 |
| A1 | 0.10 | 0.25 | 0.004 | 0.010 |
| A3 | 0.19 | 0.25 | 0.008 | 0.010 |
| b | 0.35 | 0.49 | 0.014 | 0.019 |
| D | 8.55 | 8.75 | 0.337 | 0.344 |
| E | 3.80 | 4.00 | 0.150 | 0.157 |
| e | 1.27 BSC | | 0.050 BSC | |
| H | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.019 |
| L | 0.40 | 1.25 | 0.016 | 0.049 |
| M | 0° | 7° | 0° | 7° |

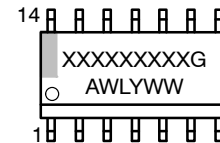
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

| | | |
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SOIC-14
CASE 751A-03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
 PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. NO CONNECTION
 5. ANODE/CATHODE
 6. NO CONNECTION
 7. ANODE/CATHODE
 8. ANODE/CATHODE
 9. ANODE/CATHODE
 10. NO CONNECTION
 11. ANODE/CATHODE
 12. ANODE/CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 2:
 CANCELLED

STYLE 3:
 PIN 1. NO CONNECTION
 2. ANODE
 3. ANODE
 4. NO CONNECTION
 5. ANODE
 6. NO CONNECTION
 7. ANODE
 8. ANODE
 9. ANODE
 10. NO CONNECTION
 11. ANODE
 12. ANODE
 13. NO CONNECTION
 14. COMMON CATHODE

STYLE 4:
 PIN 1. NO CONNECTION
 2. CATHODE
 3. CATHODE
 4. NO CONNECTION
 5. CATHODE
 6. NO CONNECTION
 7. CATHODE
 8. CATHODE
 9. CATHODE
 10. NO CONNECTION
 11. CATHODE
 12. CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 5:
 PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. ANODE/CATHODE
 5. ANODE/CATHODE
 6. NO CONNECTION
 7. COMMON ANODE
 8. COMMON CATHODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. ANODE/CATHODE
 12. ANODE/CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 6:
 PIN 1. CATHODE
 2. CATHODE
 3. CATHODE
 4. CATHODE
 5. CATHODE
 6. CATHODE
 7. CATHODE
 8. ANODE
 9. ANODE
 10. ANODE
 11. ANODE
 12. ANODE
 13. ANODE
 14. ANODE

STYLE 7:
 PIN 1. ANODE/CATHODE
 2. COMMON ANODE
 3. COMMON CATHODE
 4. ANODE/CATHODE
 5. ANODE/CATHODE
 6. ANODE/CATHODE
 7. ANODE/CATHODE
 8. ANODE/CATHODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. COMMON CATHODE
 12. COMMON ANODE
 13. ANODE/CATHODE
 14. ANODE/CATHODE

STYLE 8:
 PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. NO CONNECTION
 5. ANODE/CATHODE
 6. ANODE/CATHODE
 7. COMMON ANODE
 8. COMMON ANODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. NO CONNECTION
 12. ANODE/CATHODE
 13. ANODE/CATHODE
 14. COMMON CATHODE

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-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management